

Features

- · Excellent Package for Heat Dissipation
- · Moisture Sensitivity Level 1
- High Density Cell Design for Low R_{DS(on)}
- Halogen Free."Green" Device(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

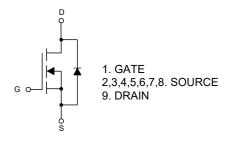
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 45°C/W Junction to Ambient (Note2)
- Thermal Resistance: 0.35°C/W Junction to Case

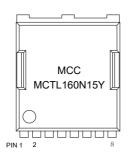
Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	150	V	
Gate-Source Volltage		V _{GS}	±25	V	
Continuous Drain Current	T _C =25°C	1	160		
	T _C =100°C	– I _D	101	A	
Pulsed Drain Current (Note3)		I _{DM}	640	Α	
Total Power Dissipation ^(Note4)		P _D	357	W	
Single Pulsed Avalanche Energy ^(Note5)		E _{AS}	200	mJ	

Note:

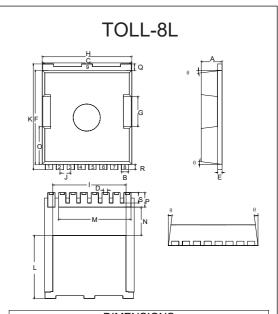
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. T_J =25°C, V_{DD} =100V, V_{GS} =10V, L=1mH

Internal Structure and Marking Code





N-CHANNEL MOSFET



DIMENSIONS					
DIM		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.028	0.035	0.70	0.90	
С	0.382	0.390	9.70	9.90	
D	0.017	0.020	0.42	0.50	
E	0.016	0.024	0.40	0.60	
F	0.405	0.417	10.28	10.58	
G	0.122	0.138	3.10	3.50	
Н	0.382	0.398	9.70	10.10	
I	0.311	0.327	7.90	8.30	
J	0.047		1.2	20	BSC
K	0.452	0.468	11.48	11.88	
L	0.266	0.281	6.75	7.15	
М	0.315		8.0	00	
N	0.118	0.130	3.00	3.30	
0	0.157	0.172	3.98	4.38	
Р	0.055	0.071	1.40	1.80	
Q	0.024	0.031	0.60	0.80	
R	0.020	0.028	0.50	0.70	
S	0.039	0.051	1.00	1.30	
θ	4°	10°	4°	10°	

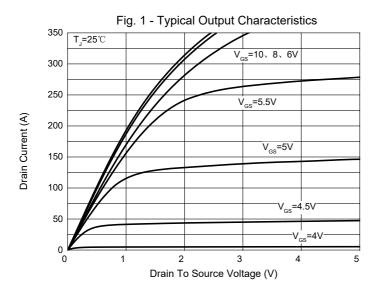


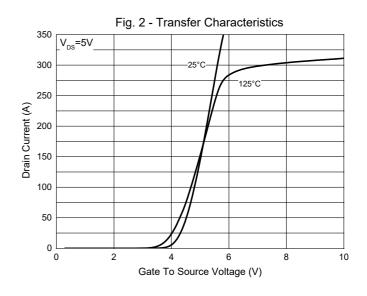
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

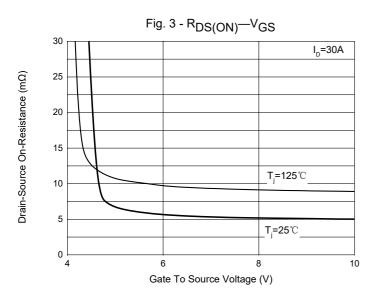
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics	-1		ļ	1			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	150			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±25V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V			1	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	3	4	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A		5.1	6.5	mΩ	
		V _{GS} =6V, I _D =20A		5.7 8			
Gate Resistance	R _g	F=1 MHz, Open drain		1.9		Ω	
Diode Characteristics			-	1			
Continuous Body Diode Current	Is				160	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.3	V	
Reverse Recovery Time	t _{rr}	L 004 H / H 4004 /		138		ns	
Reverse Recovery Charge	Q _{rr}	I _F =80A, dI _F /dt=100A/μs		499		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			9440		pF	
Output Capacitance	C _{oss}	V_{DS} =75V, V_{GS} =0V,f=1MHz		580			
Reverse Transfer Capacitance	C _{rss}			32			
Total Gate Charge	Q_g			157			
Gate-Source Charge	Q _{gs}	V _{DS} =75V,V _{GS} =10V,I _D =80A		36		nC	
Gate-Drain Charge	Q_{gd}			52		l	
Turn-On Delay Time	t _{d(on)}			38			
Turn-On Rise Time	t _r	V _{DD} =75V, V _{GS} =10V,		156		ns	
Turn-Off Delay Time	t _{d(off)}	$R_{GEN}=6\Omega$, $I_{DS}=80A$		134			
Turn-Off Fall Time	t _f			79			

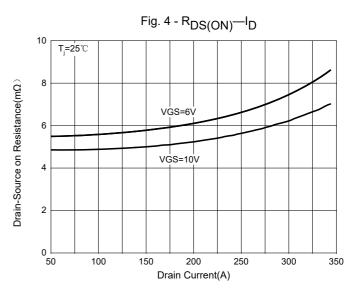


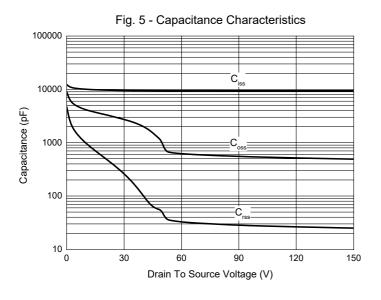
Curve Characteristics

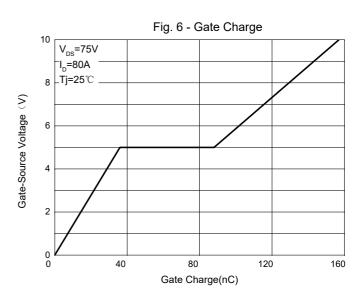






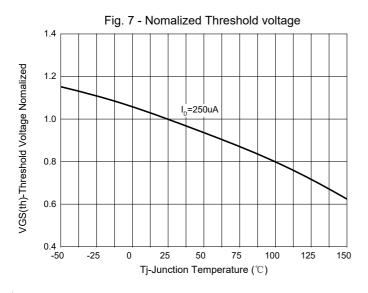


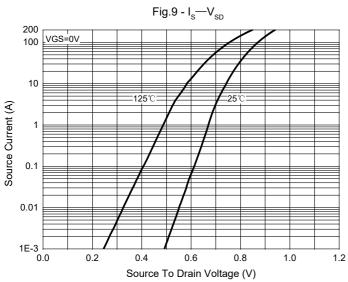


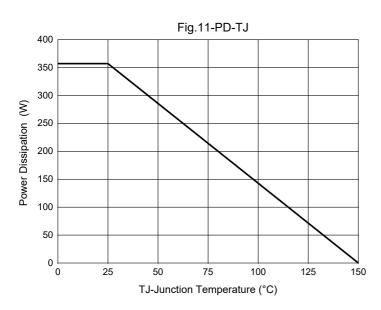


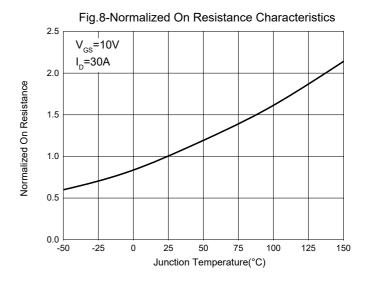


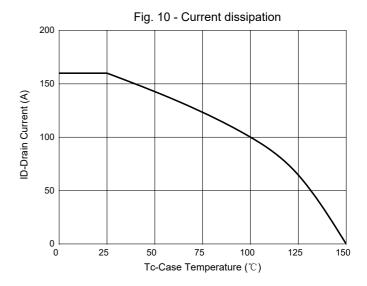
Curve Characteristics





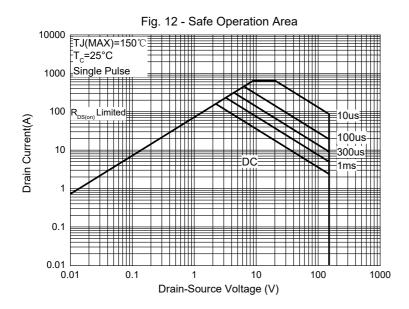


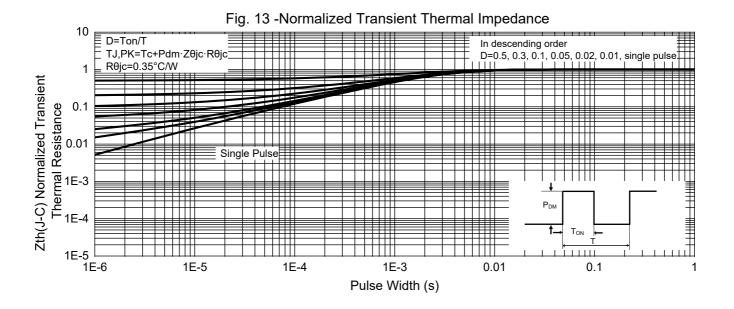






Curve Characteristics







Ordering Information

	Device	Packing
Part Number-TP		Tape&Reel: 2Kpcs/Reel

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